

# TB62731FUG

## Step-up DC-DC Converter for White LED Driver

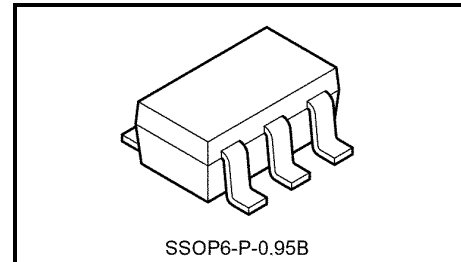
The TB62731FUG is an LED driver that uses a high power efficiency step-up DC-DC converter. The converter turns on/off 2 to 6 white LEDs in series.

The IC incorporates an N-channel MOSFET transistor used for coil-switching and a function that reduces the LED current in response to increase in temperature.

The mean LED current can be easily set using an external resistor.

The IC is ideal as a driver for LED light sources used as liquid crystal backlights for PDAs, cellular phones, and handy terminals.

The suffix (G) appended to the part number represents a Lead (Pb) -Free product.



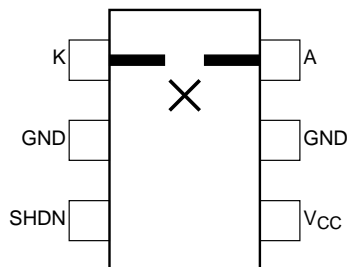
SSOP6-P-0.95B

Weight: 0.016 g (typ.)

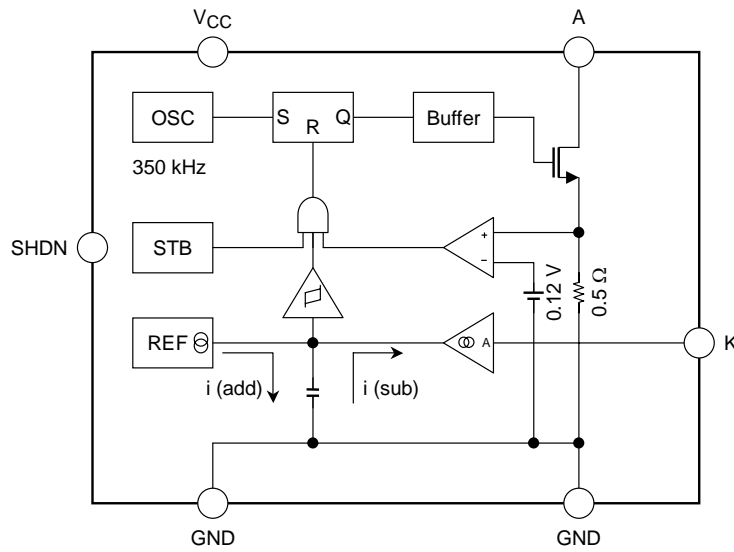
### Features

- Maximum output voltage:  $V_o \leq 28\text{ V}$
- Mean LED current values set according to external resistor
  - 14 mA (typ.) @ $R_{\text{sens}} = 2.7\ \Omega$
  - 20 mA (typ.) @ $R_{\text{sens}} = 1.8\ \Omega$
- Supply power: Up to 320 mW supported
- Compact package: SSOP6-P-0.95B, 6 pins
- Built-in temperature derating function: LED current derated automatically depending on temperature
- High power efficiency
  - Up to 80% of peak power efficiency achieved using recommended components
  - $R_{\text{on}} = 2.0\ \Omega$  (typ.) @ $V_{\text{IN}} = 3.2\sim 5.5\text{ V}$
  - Built-in low  $R_{\text{on}}$  power MOS switch

### Pin assignment (top view)



**Block Diagram**



**Pin Functions**

No	Symbol	Function
1	K	Pin connecting LED cathode to resistor used to set current. Feedback pin for voltage waveforms for controlling the LED constant current.
2, 5	GND	Ground pin for the logic
3	SHDN	IC enable pin. Low, Standby Mode takes effect and pin A is turned off.
4	V <sub>CC</sub>	Input pin for power supply for operating the IC. Operating voltage range: 3.0~5.5 V
6	A	DC-DC converter switch pin. The switch is an N-channel MOSFET transistor.

Note: Connect both GND pins to ground.

## Absolute Maximum Ratings (unless otherwise specified, $T_{opr} = 25^{\circ}\text{C}$ )

Characteristics	Symbol	Rating	Unit
Supply voltage	$V_{CC}$	-0.3~+6.0	V
Input voltage	$V_{IN}$	-0.3~+ $V_{CC} + 0.3$	V
Pin A (anode) current	$I_o$ (A)	+270	mA
Pin A voltage	$V_o$ (A)	-0.3~+28	V
Power dissipation	$P_D$	0.41 (IC only)	W
		0.47 (IC mounted on PCB) (Note)	
Saturation thermal resistance	$R_{th(j-a)} 1$	300 (IC only)	$^{\circ}\text{C/W}$
	$R_{th(j-a)} 2$	260 (IC mounted on PCB)	
Operating temperature range	$T_{opr}$	-40~+85	$^{\circ}\text{C}$
Storage temperature range	$T_{stg}$	-40~+150	$^{\circ}\text{C}$
Maximum junction temperature	$T_j$	125	$^{\circ}\text{C}$

Note: The power dissipation is derated by 3.8 mW/ $^{\circ}\text{C}$  from the Absolute maximum rating for every  $1^{\circ}\text{C}$  exceeding the ambient temperature of  $25^{\circ}\text{C}$  (when the IC is mounted on a PCB).

## Recommended Operating Conditions (unless otherwise specified, $T_{opr} = -40\sim 85^{\circ}\text{C}$ )

Characteristics	Symbol	Test circuit	Test condition	Min	Typ.	Max	Unit
Supply voltage	$V_{CC}$	—	—	3.0	—	4.3	V
SHDN pin high-level input voltage	$V_{IH}$	—	—	$V_{CC} - 0.5$	—	$V_{CC}$	V
SHDN pin low-level input voltage	$V_{IL}$	—	—	0	—	0.5	V
SHDN pin high-level input pulse width	tpw SHDN	—	—	500	—	—	$\mu\text{s}$
Set LED current (mean)	$I_o$	—	$V_o$ (A) = $V_{IN}$ 3.0 V, $V_{OUT}$ 16 V	5	—	20	mA

## Electrical Characteristics (unless otherwise specified, Ta = -40~85°C, VCC = 3.0~5.5 V)

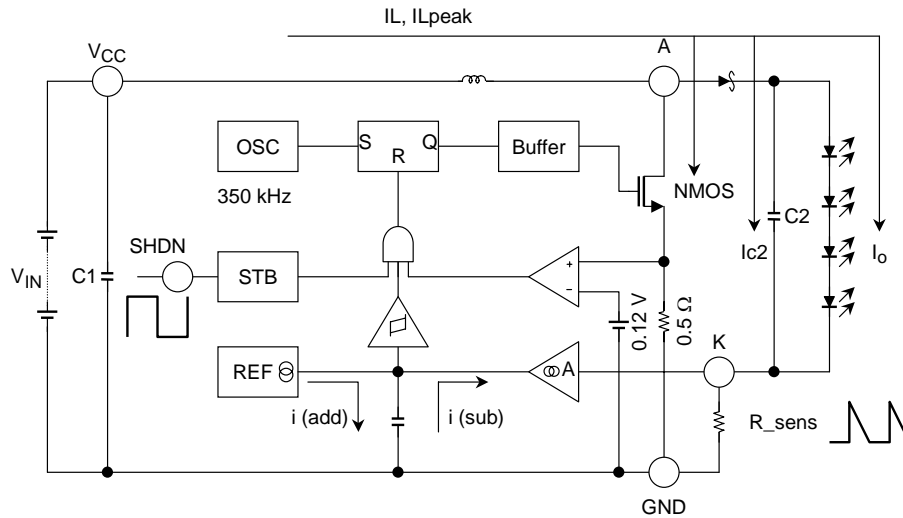
Characteristics	Symbol	Test circuit	Test condition	Min	Typ.	Max	Unit
Supply voltage	V <sub>CC</sub>	—	—	3.0	—	5.5	V
Current consumption at operation	I <sub>CC</sub> (ON)	—	V <sub>CC</sub> = 3.6 V	—	0.6	0.9	mA
Current consumption at standby	I <sub>CC</sub> (SHDN)	—	SHDN = 0 V	—	0.5	1.0	μA
SHDN pin current	I <sub>SHDN</sub>	—	SHDN = V <sub>CC</sub> , Built-in pull-down resistor	—	4.2	7	μA
Internal MOS transistor on-resistance	R <sub>on</sub>	—	I (A) ≤ 270 mA, Including detected resistance	—	2.0	2.5	Ω
Internal MOS transistor switching frequency	f <sub>osc</sub>	—	—	275	350	425	kHz
Pin A voltage	V <sub>o</sub> (A)	—	—	28	—	—	V
Pin A current	I <sub>o</sub> (A)	—	—	210	240	270	mA
Pin A leakage current	I <sub>oz</sub> (A)	—	—	—	0.5	1	μA
Set LED current (mean)	I <sub>o</sub>	—	V <sub>CC</sub> = 3.2~4.2 V, R <sub>sens</sub> = 1.8 Ω T <sub>opr</sub> = 25°C (Note 1)	17.6	20	22.4	mA
Pin K derating start ambient temperature	T <sub>del</sub>	—	Equivalent to R <sub>sens</sub> = 1.8 Ω, L = 4.7 μH, V <sub>o</sub> = 16 V	—	45 (Note 2)	—	°C

Note 1: Due to operation of the temperature derating function, measure when Ta = 25°C.

Note that fluctuation in R<sub>sens</sub> resistors is not included in the specified value.

I<sub>o</sub> may be different from the specified value due to the relation between the inductor value and load.

Note 2: This rating is guaranteed by the design.



**Figure 1 Application Circuit**

The basic TB62731FUG circuit uses a step-up DC-DC converter and burst control of the current pulse.

**Basic Operation**

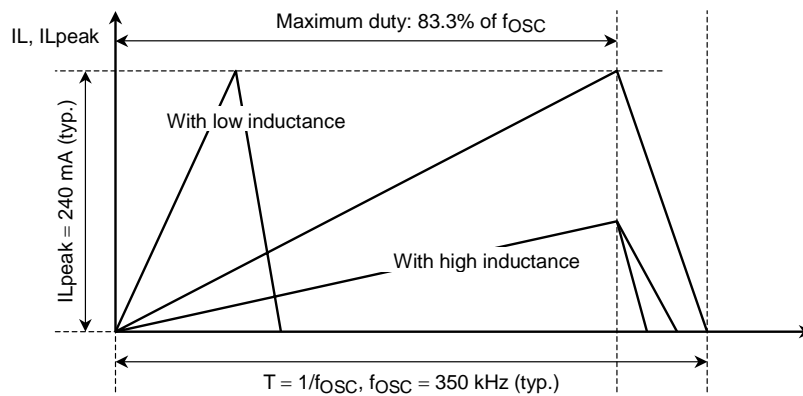
The internal MOS transistor (NMOS) is turned on at  $f_{OSC} = 350 \text{ kHz}$ , charging energy to the inductor.

The inductance current  $I_L$  increases from 0. When  $I_L = I_{Lpeak} = 240 \text{ mA}$  (typ.) or when  $5/6$  (83.3%) of  $f_{OSC}$  (= 350 kHz) is reached, the transistor is turned off.

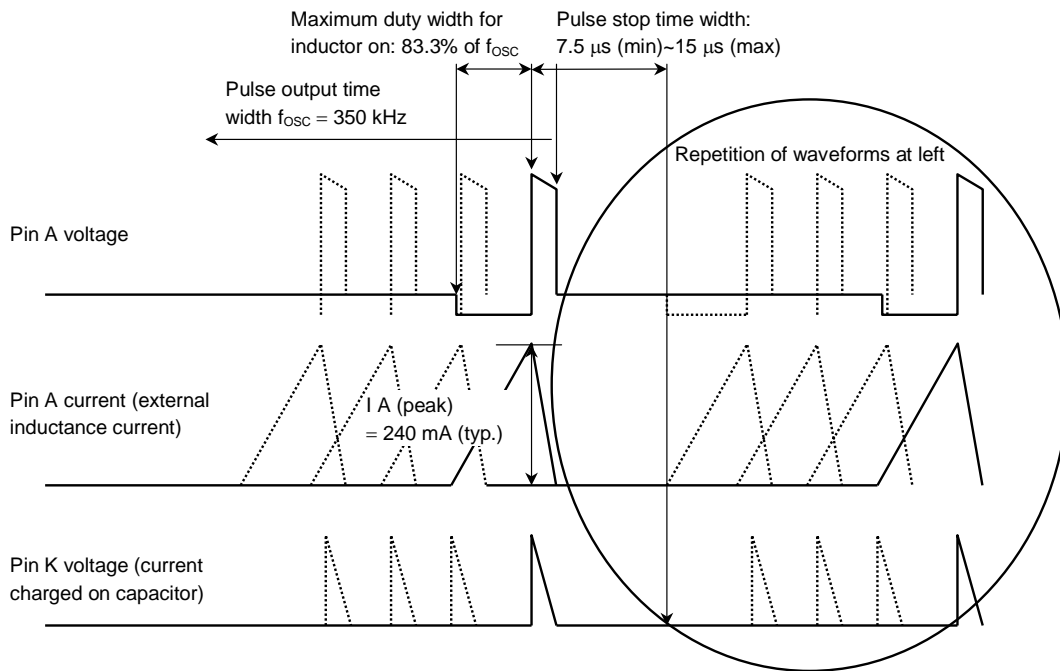
At that time, the coil maintains  $I_L = I_{Lpeak}$ , the Schottky diode is turned on, and  $I_L = I_{c2}$  flows. Then,  $I_{c2}$  decreases, reaching  $I_L = 0$ .

The above operation repeats. When  $I_{c2}$  is fully charged, the surplus current becomes  $I_o$ , which flows to the LED.

The graph below shows details of the basic pulse used for burst control.



**Figure 2 Switching Waveform of Inductance**



**Figure 3 Burst Control Waveforms**

### Burst Control

Burst control is control of the number of current pulses, shown in the graph on the previous page. Control is repeated in desired cycles. The current pulse in the graph is the charged current on capacitor 2 (C2) for output.

The current pulse is supplied to the LED as current discharged from the output-side capacitor. The current pulse flows to GND via R\_sens.

The waveform of the voltage charged on the output-side capacitor is fed back to the IC from pin K via C2.

The internal circuit which uses pin K for input controls the number of current pulses so that the mean voltage value of the obtained voltage waveform is 36 mV. As a result, the output current is controlled as the constant current (= mean current).

Connecting R\_sens = 1.8 Ω obtains the mean current (36 mV ÷ 1.8 Ω = 20 mA).

Current is controlled by PFM (pulse frequency modulation) because the time when the output pulse is generated varies (increases/decreases).

A prerequisite is that the input power from V<sub>IN</sub> is larger than the output power to the LED load. The constant current is maintained by fixing a pulse stop time of 7.5~15 μs and increasing/decreasing the number of current pulses. The number of current pulses is fewer when the input power exceeds the output power, larger when the input power is less than the output power.

The burst frequency (pulse generation frequency) at controlled constant current is calculated as follows:  
 $f_{burst} [\text{Hz}] = (\text{number of current pulses} \times (1/275 \sim 1/350 \text{ kHz}) + \text{pulse stop time} (7.5 \sim 15 \mu\text{s})) \dots \text{ formula 1}$

The IC is designed to supply a load power of 320 mW (min).

Generally, a step-up inductance of 47 μH is used for optimum design for the load power of 320 mW. When the load power is small, the inductance must be small.

Make sure the following condition for LED load between pins A and K is satisfied:

$$V_{IN} (V_{CC}) < \text{LED } V_f \text{ total}$$

Note that, regardless of control by the IC, LEDs are always on.

## Standby Operation

The SHDN pin is used to set normal or standby operation. When SHDN is set to Low, the operation is standby; when the pin is High, the LED is turned on. Current consumption in Standby Mode is 1  $\mu$ A (max).

## Output-side capacitor setting

When the output-side capacitor (C2) = 0.1  $\mu$ F, the peak current to be supplied to LEDs is expected to be the set current +5~+8 mA.

When C2 = 0.01  $\mu$ F, the peak current is expected to be the set current +20~30 mA; when C2 = 1  $\mu$ F, it is the set current +2~3 mA. Toshiba recommend C2 = 1  $\mu$ F or more considering the LED max If.

The IC is used only for lighting LEDs. The IC does not finely control output current ripples. This is because eliminating ripples is considered unnecessary as the LED emittance is recognized as the integral amount.

## External inductance setting

The minimum external inductance is calculated as follows:

$$L (\mu\text{H}) = ((K \times P_o) - V_{\text{IN min}} \times I_o) \times (1/f_{\text{OSC min}}) \times 2 \times (1/I_p \text{ min} \times I_p \text{ min}) \dots \text{ formula 2}$$

The above parameters are described below:

$P_o$ : output power (power required by LED load)

$$P_o (\text{W}) = V_f \text{ LED} \times I_f \text{ LED} + V_f \text{ schottky} \times I_f \text{ LED} + R_{\text{sens}} \times I_f \text{ LED} \times I_f \text{ LED}$$

LED forward current:  $I_f \text{ LED}$  (mA) = Set current:  $I_o$  (mA), LED forward voltage:  $V_f \text{ LED}$  (V),

schottky diode forward voltage:  $V_f \text{ schottky}$  (V),

Setting resistance:  $R_{\text{sens}}$  ( $\Omega$ )

$V_{\text{IN min}}$  (V): minimum input voltage (battery voltage)

If the input voltage includes a resistance component, take the voltage drop into consideration for the minimum input voltage.

The input current  $I_{\text{IN}}$  is roughly estimated as follows:

$$I_{\text{IN}} (\text{mA}) = V_f \text{ LED} \times I_o \times (1/\eta) \times (1/V_{\text{IN}}) \dots \text{ formula 3}$$

When  $\text{min } V_{\text{IN}} = 3.2$  (V),  $V_f \text{ LED} = 16$  (V),  $I_o = 18$  (mA), and  $\eta \geq 75$  (%), then  $I_{\text{IN}} = 0.12$  (mA). As a result, the voltage drops by 1.2 V due to the 1- $\Omega$  DC resistance component. Because the IC's minimum  $V_{\text{CC}} = 3.0$  V, the minimum  $V_{\text{IN}}$  is 3.12 V ( $V_{\text{IN}} \geq 3.12$  V).

$I_o$  (A): Mean current value set according to resistance  $R_{\text{sens}}$  ( $\Omega$ )

$f_{\text{OSC}}$  (Hz): Switching frequency of internal MOS transistor

Specified values for  $f_{\text{OSC}}$  (kHz): 275 min, 350 typ., 475 max

$I_p$  (A): Peak current value supplied to external inductor

Specified values for  $I_p$  (A): 230 min, 240 typ., 270 max

K: Margin of output power  $K = 1.1 \sim 1.3$

The ideal condition is to give 1.05 to 1.3 times the output power  $P_o$  as the input power.

The loss of the IC is assumed to be included in the margin.

If K is too large, it may not be possible for the current characteristic to be the specified value. Note that  $K > 1$ .

Substitute the following conditions in formula 2.

Supply voltage  $V_{IN} = 3.0\sim 4.3$  (V)

Output-side capacitor  $C2 = 1$  ( $\mu\text{F}$ ) . . .  $C2$  is ignored in the calculation.

Where it is assumed that,

$V_{fLED} = 16$  (V),  $V_{f\text{ schottky}} = 0.3$  (V),  $R_{\text{ sens}} = 1.8$  ( $\Omega$ ),  $I_o = 20$  (mA),  $K = 1.1$

$V_{fLED}$ : LED  $V_f$

$V_{f\text{ schottky}}$ : schottky diode  $V_f$

$R_{\text{ sens}}$ : setting resistance

$I_o$ : set current

$K$ : margin

$$L (\mu\text{H}) = ((1.1 \times 16 \times 0.02) - 3 \times 0.02) \times (1/275e3) \times 2 \times (1/(0.21 \times 0.21)) = 48.1 (\mu\text{H}, V_{IN} = 3.0 \text{ V})$$
$$43.8 (\mu\text{H}, V_{IN} = 4.3 \text{ V})$$

Thus, 48.1 ( $\mu\text{H}$ ) is selected when the input voltage is low, 3.0 V.

Note that the calculation does not consider fluctuations in inductance. Toshiba recommend selection of an inductance of 1.2 times the calculated value.

The recommended inductance under the above conditions is  $L (\mu\text{H}) = 48.1 (\mu\text{H}) \times 1.2 \geq 57.7 (\mu\text{H})$ .



**Selection of R\_sens**

Resistance between pin K and GND R\_sens (Ω) is used for setting output current I<sub>o</sub>. The mean output current I<sub>o</sub> can be set according to the resistance.

The mean current I<sub>o</sub> (mA) to be set is roughly calculated as follows:

$$I_o \text{ (mA)} = 36 \text{ (mV)} \div R_{\text{sens}} \text{ (}\Omega\text{)}$$

For example, when R\_sens = 1.8 (Ω), I<sub>o</sub> = 20 (mA).

Take a current error of ±10% (not including R\_sens error) into consideration.

The IC has a minimum output P<sub>o</sub> = 320 (mA, choke coil = 47 μH).

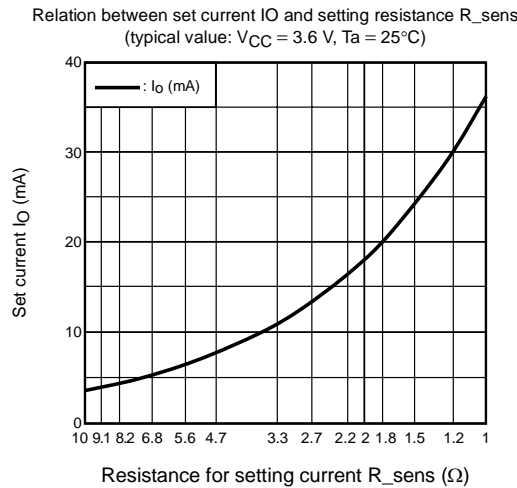
At that time, if the product of mean current I<sub>o</sub> and output voltage V<sub>o</sub> exceeds P<sub>o</sub> = 320 (mW), mean current I<sub>o</sub> may become less than the desired value.

If the IC is not connected to the output-side capacitor (for smoothing), the set current I<sub>o</sub> can be obtained.

At that time, because the current flowing to the LED is a pulse current with a maximum peak value of 270 mA, make sure that surge current I<sub>FP</sub> (mA) does not flow to the LED.

Toshiba recommend use of components with low reactance (parasitic inductance) and minimized PCB wiring.

Toshiba also recommend allocating components in the application circuit diagram as near each other as possible.



**Figure 4**

## Output Derating Function

Toshiba recommend derating the LED current depending on the increase in ambient temperature. The TB62731FUG is designed to ensure safe and efficient driving of white LEDs used as backlight sources for color LCDs. The IC incorporates a function that derates current according to the set temperature (the ambient temperature when the IC is mounted),  $T_a$ .

The IC features an output current that varies according to the internally-detected temperature  $T_{js}$  as follows: when  $T_{js} = 45$  (°C), output current is 100%; when  $T_{js} = 100$  (°C), output current is 0%.

The derating start temperature  $T_s$  (°C) is determined based on  $T_a$  ( $T_a = T_s$  when the IC is not operating) by subtracting the self-generated temperature  $T_{up}$  (°C) from  $T_{js} = 45$  (°C).

$$T_s \text{ (}^\circ\text{C)} = 45 \text{ (}^\circ\text{C)} - T_{up} \text{ (}^\circ\text{C)} \dots \text{formula 4}$$

The derating characteristic is as shown in the graph below, Figure 5, which shows the relation between output current change ratio and internally-detected temperature (IC temperature)  $T_{js}$ .

The self-generated temperature  $T_{up}$  (°C) is calculated as follows:

$$T_{up} \text{ (}^\circ\text{C)} = (P \text{ loss (W)} - P \text{ parts (W)}) \times \theta_{ja} \text{ (}^\circ\text{C/W)} \dots \text{formula 5}$$

P loss: power loss

P parts: power loss of parts

$\theta_{ja}$ : package saturation thermal resistance ( $\Omega$ )

The parameters are described below:

DC resistance of inductor: RDC ( $\Omega$ )

LED forward current: If LED (A)

LED forward voltage: Vf LED (V)

Schottky diode forward voltage: Vf schottky (V)

Setting resistance: R\_sens

$$P \text{ loss (W)} \approx P_o \text{ (W)} \div \eta \text{ (\%)} - P_o \text{ (W)}$$

$P_o$ : output power

$\eta$ : power efficiency

$$P \text{ parts (W)} \approx RDC \times I_{IN} + Vf \text{ schottky} \times I_{LED} + R_{sens} \times I_{LED} \times I_{LED}$$

$$\theta_{ja} \text{ (}^\circ\text{C/W)} \leq 260 \text{ (}^\circ\text{C/W)}$$

max when IC mounted on PCB

$$P_o \text{ (W)} = V_o \text{ (V)} \times I_o \text{ (A)}$$

$V_o$ : Vf LED output voltage

$I_o$ : mean output current = set current

$$P_i \text{ (W)} = V_{IN} \text{ (V)} \times I_{IN} \text{ (A)}$$

$P_i$ : input power

$V_{IN}$ : input voltage

$I_{IN}$ : mean input current

$$\eta \text{ (\%)} = 100 \times P_o \text{ (W)} \div P_i \text{ (W)}$$

Example of calculation: Where the measurement result for any lighting circuit shows the following values:

RDC = 0.5 ( $\Omega$ ),  $P_o = 320$  (mW),  $I_{IN} = 0.1$  (mA),  $I_o = 20$  (mA),  $R_{sens} = 1.8$  ( $\Omega$ ), Vf schottky = 0.3 (V), and  $\eta = 70$  (%)

The self-generated temperature  $T_{up}$  (°C) is calculated as follows:

$$T_{up} (\text{°C}) = ((0.32 - (0.32 \times 0.7)) - (0.5 \times 0.1 + 0.3 \times 0.02 + 1.8 \times 0.02 \times 0.02)) \times 260 = 10.2 (\text{°C})$$

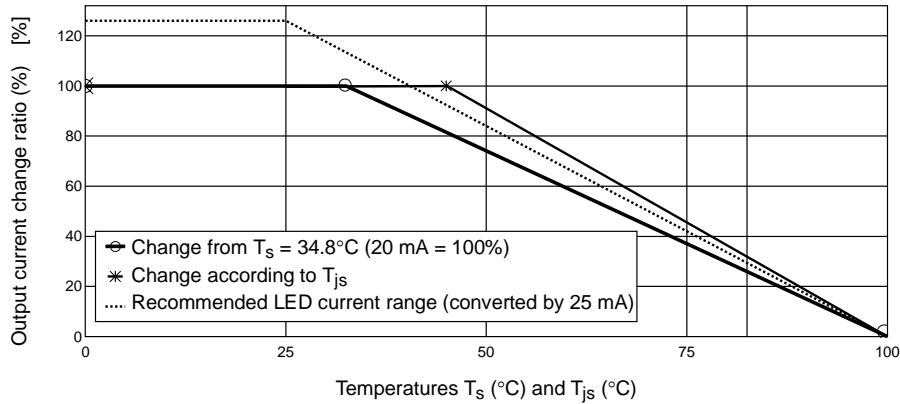
Thus, the derating start temperature  $T_s$  (°C) is calculated as follows:

$$T_s (\text{°C}) = 45 (\text{°C}) - 10.4 (\text{°C}) = 34.8 (\text{°C})$$

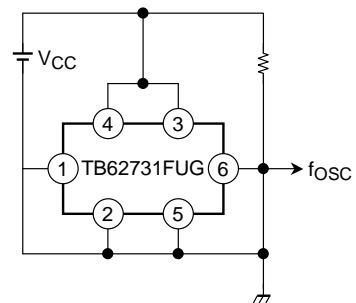
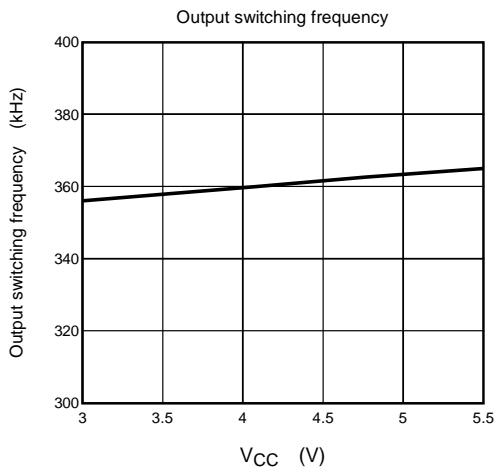
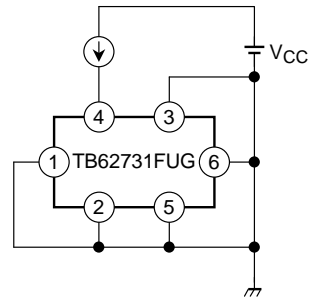
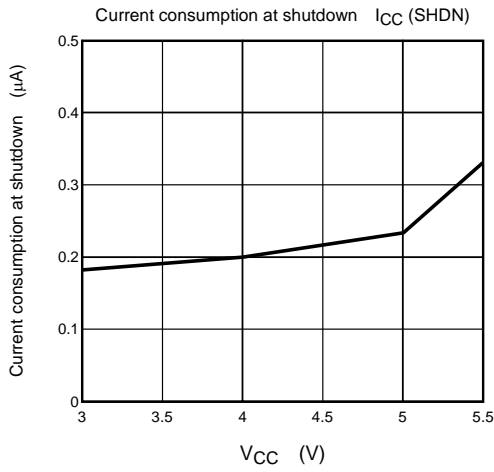
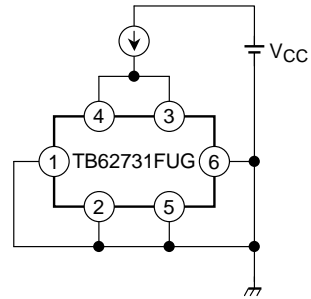
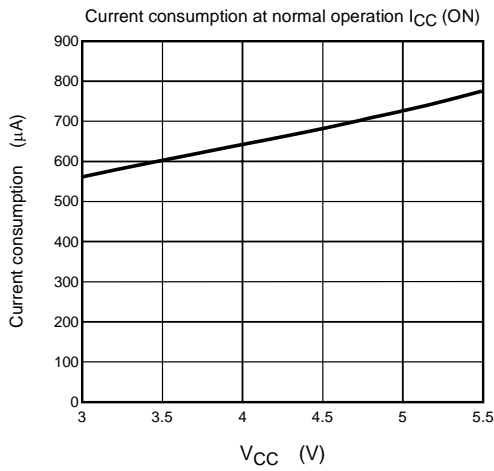
As a result,  $I_o$  is controlled in the recommended current range as shown in Figure 5.

Since saturation thermal resistance  $\theta_{ja} = 260$  (°C/W) is the maximum value,  $\theta_{ja} = 210\sim 260$  (°C/W) is used as a mounting condition.

Depending on the IC characteristics, peripherals, and use environment, the derating start temperature fluctuates among ICs.

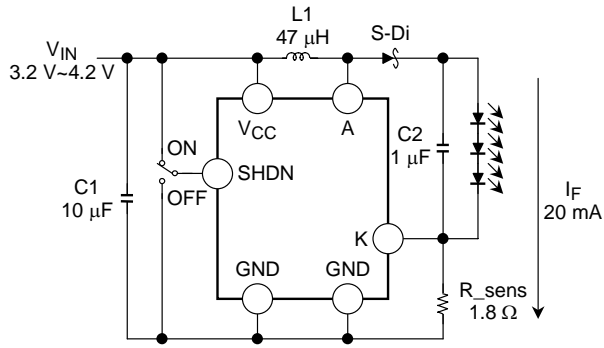


**Figure 5 Derating Function of Set Current**

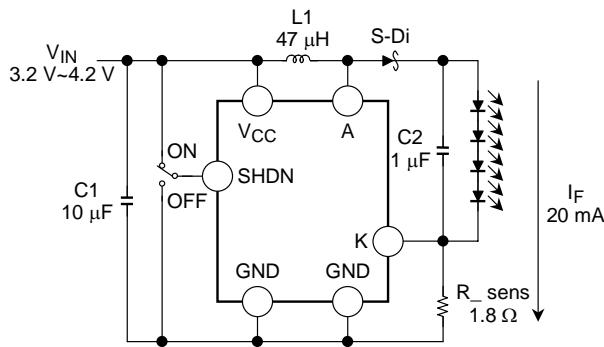
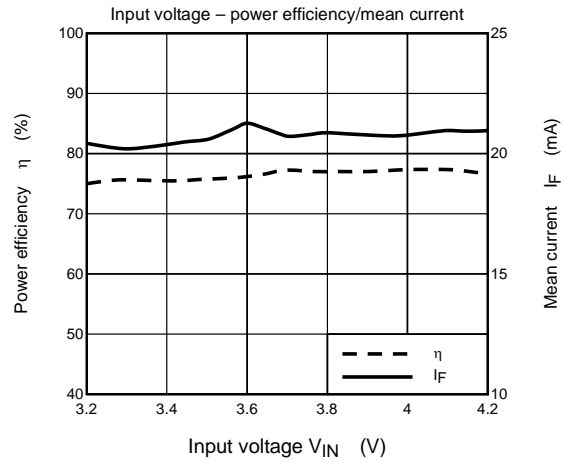


## Application Circuit Example 1 (characteristic using recommended coil as reference)

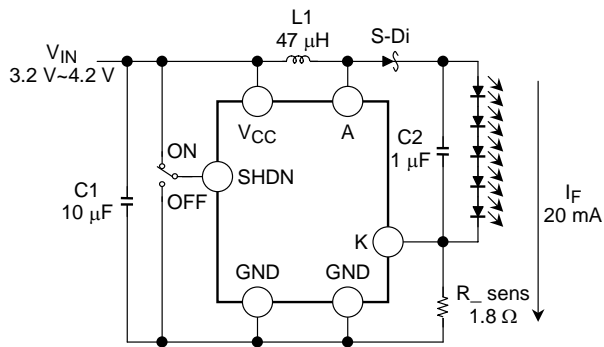
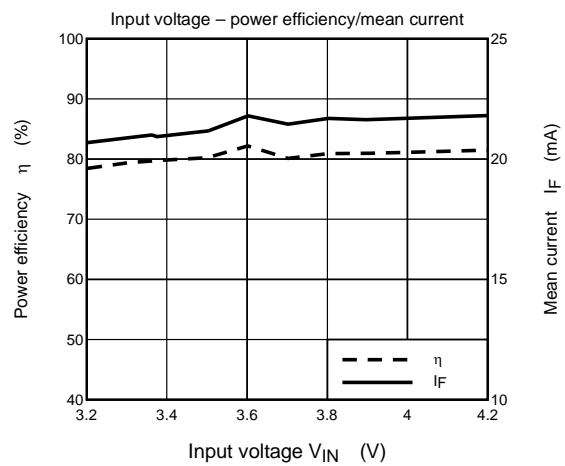
Though it is necessary to consider the DC resistance of L1, an inductance of 33 to 47 (typ.) to 68  $\mu\text{H}$  is suitable for turning on four LEDs.



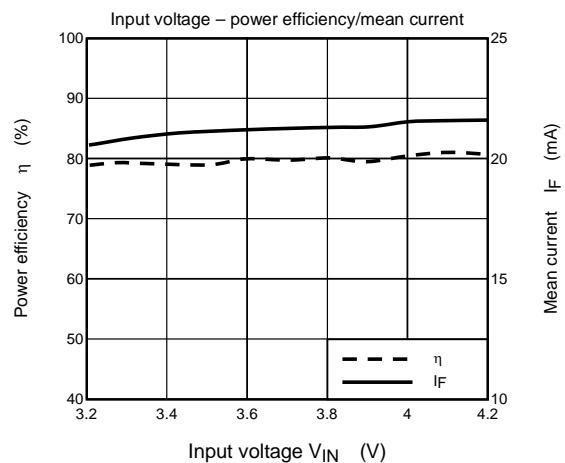
L1: Toko A914BYW-470M  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Rohm MCR03-1R8



L1: Toko A914BYW-470M  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Rohm MCR03-1R8

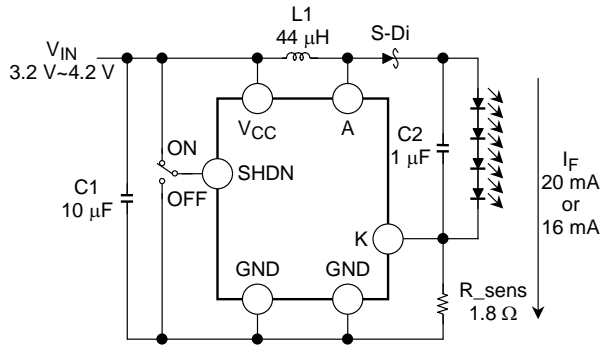


L1: Toko A914BYW-470M  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Rohm MCR03-1R8

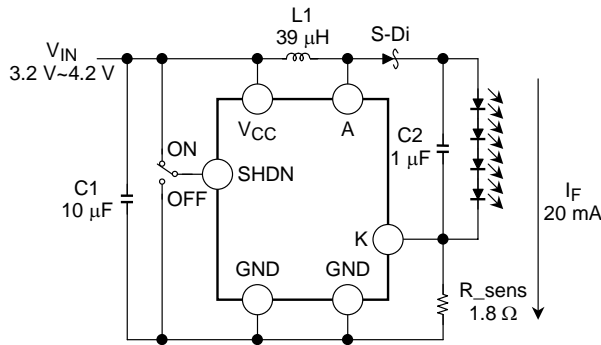
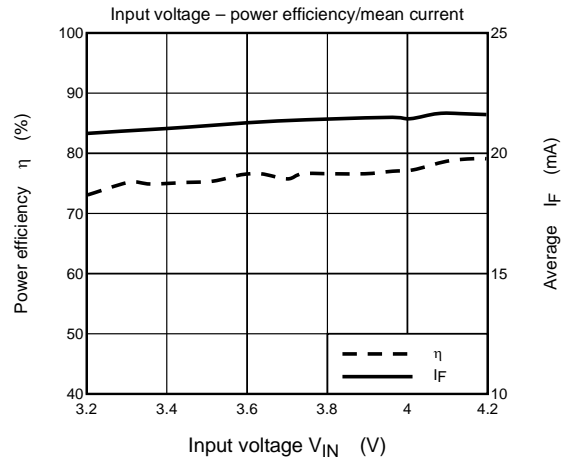


## Application Circuit Example 2 (characteristic using flat coil for handy terminal as reference)

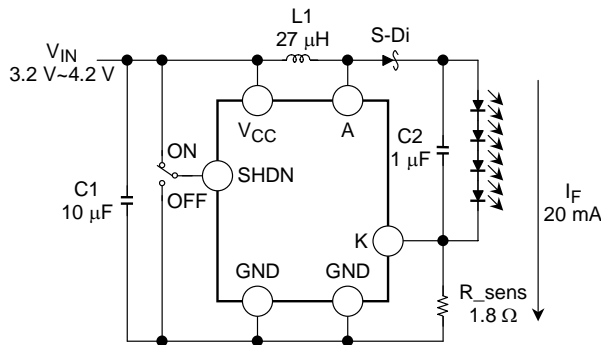
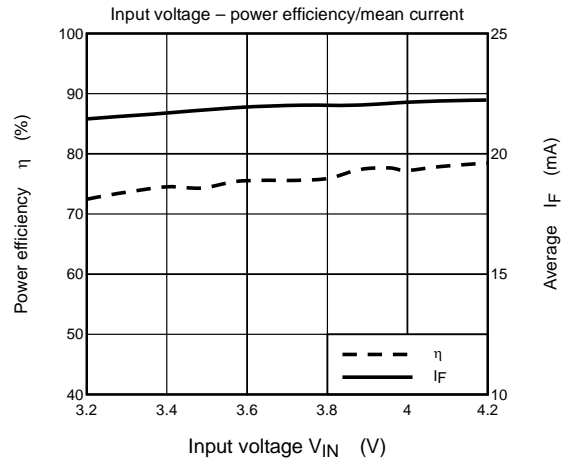
Flat coils suitable for handy terminals have a large DC resistance; thus, the power efficiency drops slightly, to about 70%.



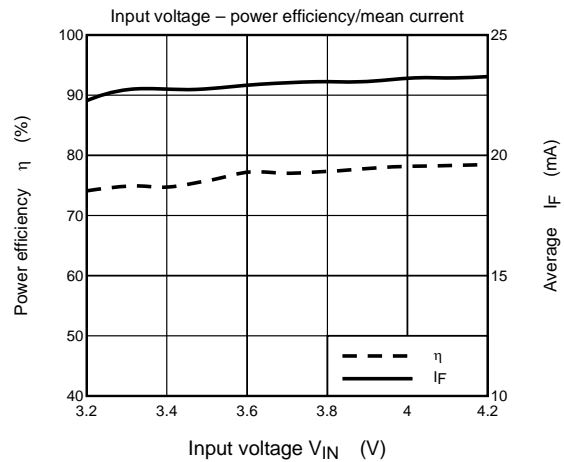
L1: TDK LDR344812T-440  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Rohm MCR03-1R8

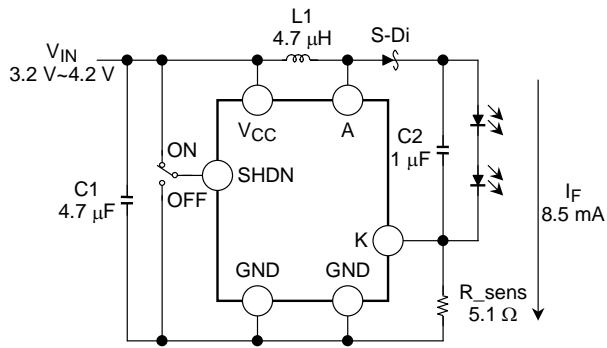


L1: TDK LDR344812T-390  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Susumu RL0510S-1R8

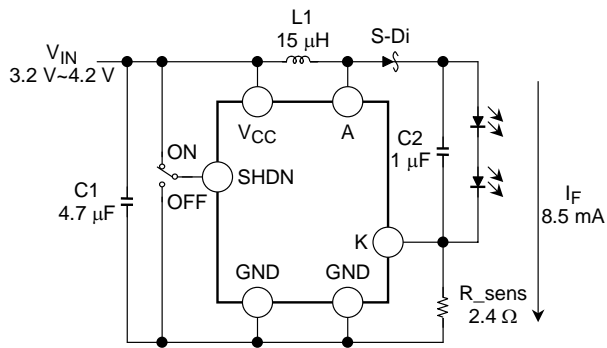
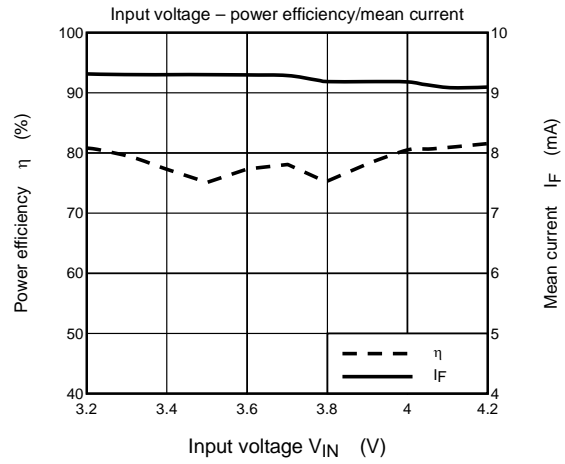


L1: Toko A914BYW-270M  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: Susumu RL0510S-1R8

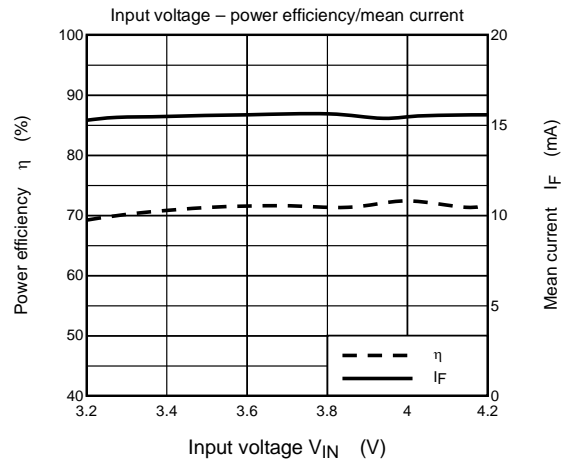




L1: Toko A914BYW-4R7  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: —



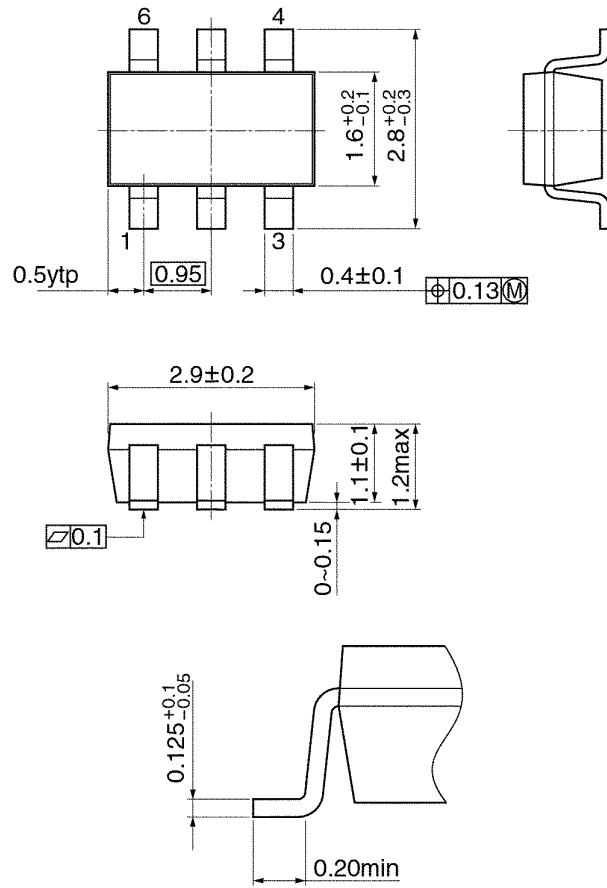
L1: Sumitomo Special Metals CXLD (CXAD) 120-150  
 S-Di: Toshiba 1SS404 20 V/1A  
 LED: Nichia NSCW215T  
 R\_sens: —



## Package Dimensions

SSOP6-P-0.95B

Unit: mm



Weight: 0.016 g (typ.)



## Notes on Contents

### 1. Block Diagrams

Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purposes.

### 2. Equivalent Circuits

The equivalent circuit diagrams may be simplified or some parts of them may be omitted for explanatory purposes.

### 3. Timing Charts

Timing charts may be simplified for explanatory purposes.

### 4. Application Circuits

The application circuits shown in this document are provided for reference purposes only.

Thorough evaluation is required, especially at the mass production design stage.

Toshiba does not grant any license to any industrial property rights by providing these examples of application circuits.

### 5. Test Circuits

Components in the test circuits are used only to obtain and confirm the device characteristics. These components and circuits are not guaranteed to prevent malfunction or failure from occurring in the application equipment.

## IC Usage Considerations

### Notes on Handling of ICs

- (1) The absolute maximum ratings of a semiconductor device are a set of ratings that must not be exceeded, even for a moment. Do not exceed any of these ratings.  
Exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.
- (2) Use an appropriate power supply fuse to ensure that a large current does not continuously flow in case of over current and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead smoke or ignition. To minimize the effects of the flow of a large current in case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- (3) If your design includes an inductive load such as a motor coil, incorporate a protection circuit into the design to prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or the negative current resulting from the back electromotive force at power OFF. IC breakdown may cause injury, smoke or ignition.  
Use a stable power supply with ICs with built-in protection functions. If the power supply is unstable, the protection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- (4) Do not insert devices in the wrong orientation or incorrectly.  
Make sure that the positive and negative terminals of power supplies are connected properly. Otherwise, the current or power consumption may exceed the absolute maximum rating, and exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.  
In addition, do not use any device that is applied the current with inserting in the wrong orientation or incorrectly even just one time.

- (5) Carefully select external components (such as inputs and negative feedback capacitors) and load components (such as speakers), for example, power amp and regulator.
- If there is a large amount of leakage current such as input or negative feedback condenser, the IC output DC voltage will increase. If this output voltage is connected to a speaker with low input withstand voltage, overcurrent or IC failure can cause smoke or ignition. (The over current can cause smoke or ignition from the IC itself.) In particular, please pay attention when using a Bridge Tied Load (BTL) connection type IC that inputs output DC voltage to a speaker directly.

**Points to Remember on Handling of ICs**

## (1) Heat Radiation Design

In using an IC with large current flow such as power amp, regulator or driver, please design the device so that heat is appropriately radiated, not to exceed the specified junction temperature ( $T_j$ ) at any time and condition. These ICs generate heat even during normal use. An inadequate IC heat radiation design can lead to decrease in IC life, deterioration of IC characteristics or IC breakdown. In addition, please design the device taking into consideration the effect of IC heat radiation with peripheral components.

## (2) Back-EMF

When a motor rotates in the reverse direction, stops or slows down abruptly, a current flow back to the motor's power supply due to the effect of back-EMF. If the current sink capability of the power supply is small, the device's motor power supply and output pins might be exposed to conditions beyond absolute maximum ratings. To avoid this problem, take the effect of back-EMF into consideration in system design.

About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-37Pb solder Bath
    - solder bath temperature = 230°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - solder bath temperature = 245°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux

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060116EBA

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